

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3050K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =30V,I_D =50A

 $R_{DS(ON)} < 11m\Omega @ V_{GS}=10V$ (Typ:8m Ω)

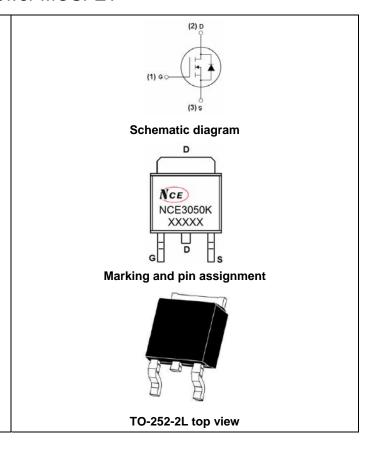
 $R_{DS(ON)}$ < 16m Ω @ V_{GS} =4.5V (Typ:10m Ω)

- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

100% UIS TESTED! 100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3050K	NCE3050K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	50	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	35.4	Α
Pulsed Drain Current	I _{DM}	200	Α
Maximum Power Dissipation	P _D	60	W
Derating factor		0.4	W/℃
Single pulse avalanche energy (Note 5)	Eas	100	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}\mathbb{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	2.5	°C/W



Electrical Characteristics (Tc=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics	<u> </u>			l .			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =250μA	1	1.6	2.6	V	
Drain-Source On-State Resistance		V _{GS} =10V, I _D =20A	-	8	11	mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	10	16		
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A		20	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	\/ -45\/\/ -0\/	-	2000	-	PF	
Output Capacitance	C _{oss}	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	280	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVID2	-	210	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	10	-	nS	
Turn-on Rise Time	t _r	V _{DD} =15V,I _D =20A	-	8	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1.8 Ω	-	25	-	nS	
Turn-Off Fall Time	t _f		-	5	-	nS	
Total Gate Charge	Qg	\/ -40\/1 -20A	-	32.3	-	nC	
Gate-Source Charge	Q_{gs}	$V_{DS}=10V,I_{D}=20A,$ $V_{GS}=10V$	-	4.9	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	6.9	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	0.85	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	50	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, I _F = 20A	-	-	27	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	-	20	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

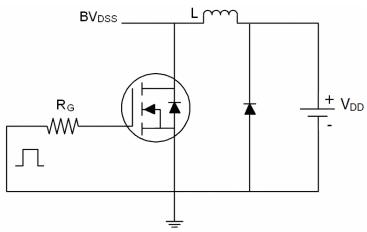
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C, V_{DD}=15V,V_G=10V,L=0.5mH, Rg=25 Ω

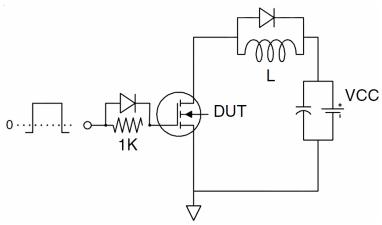


Test circuit

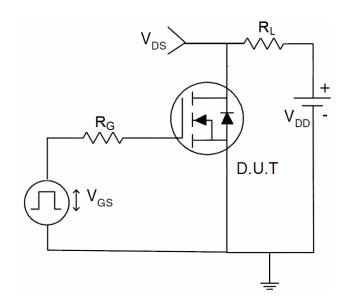
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

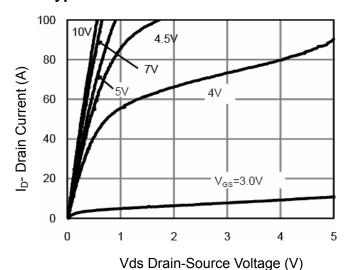


Figure 1 Output Characteristics

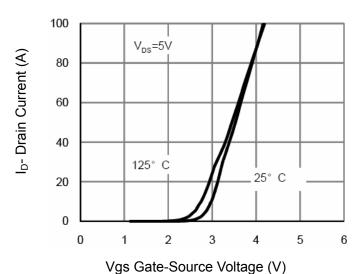


Figure 2 Transfer Characteristics

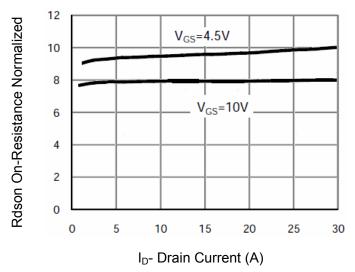


Figure 3 Rdson- Drain Current

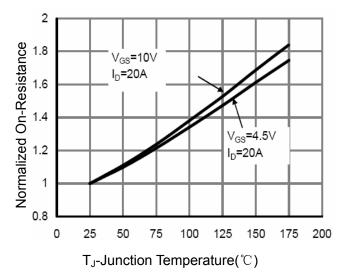


Figure 4 Rdson-JunctionTemperature

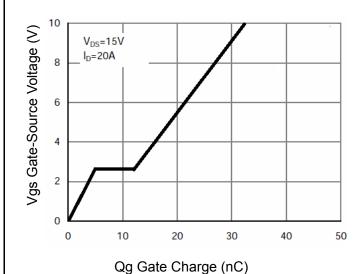


Figure 5 Gate Charge

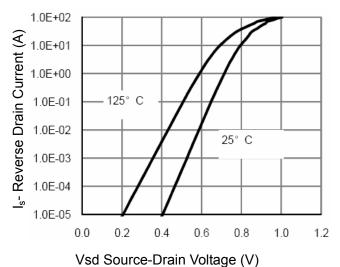


Figure 6 Source- Drain Diode Forward



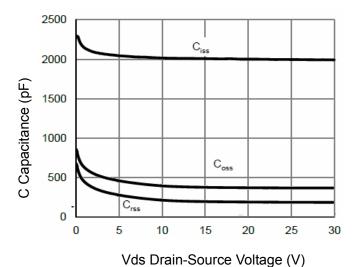
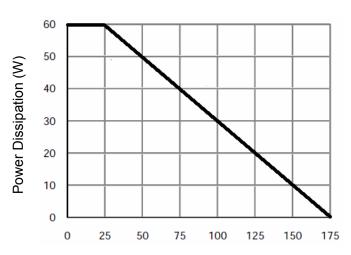


Figure 7 Capacitance vs Vds



 T_J -Junction Temperature($^{\circ}$ C) **Figure 9 Power De-rating**

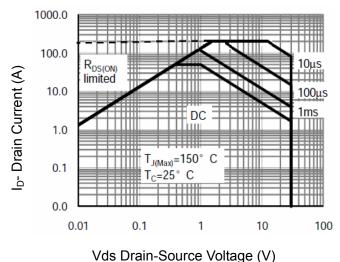


Figure 8 Safe Operation Area

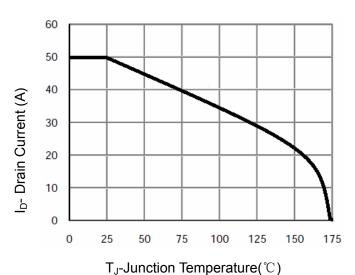
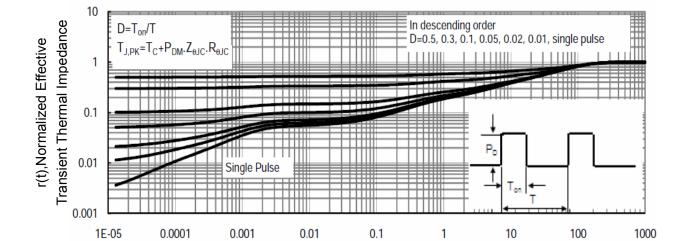


Figure 10 ID Current- Junction Temperature

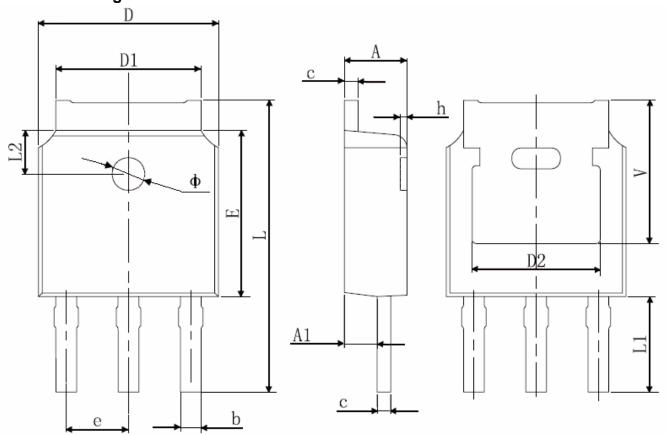


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-251S Package Information



Combal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.860	1.160	0.034	0.046	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	10.400	11.000	0.409	0.433	
L1	3.300	3.700	0.130	0.146	
L2	1.600 REF.		0.063 REF.		
Ф	1.100	1.300	0.043	0.051	
h	0.000	0.300	0.000	0.012	
V	5.350 REF.		0.211 REF.		

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